EAST Search History

EAST Search History (Prior Art)

Ref#	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L24	8	"596126".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 22:02
L19	5 4	(luminous or light near emitt\$3 or active or single quantum well or SQW)same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d}"%" or "80""%") or ("0.5" or "0.6" or "0.7" or "0.8"))and (InGaN or "In.sub.x Ga.sub.1-x N" or "In.subalpha.Ga.sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGal nN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 21:48
L18	4 3	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3) same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d}"%" or "80""%") or ("0.5" or "0.6" or "0.7" or "0.8"))and (InGaN or "In.sub.x Ga.sub.1-x N" or "In.sub.x lpha.Ga. sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGalnN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	*ADJ	ON	2010/11/05 21:42

L17	138	same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d}"%" or "80""%") or (".5{d}" or "1")) and (InGaN or "In.sub.x Ga.sub.1-x N" or "In.subalpha.Ga. sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGal nN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	Z	2010/11/05 21:41
16	1 1	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d}"%" or "80""%") or (".5{d}")) and (InGaN or "In.sub. x Ga.sub.1-x N" or "In. subalpha.Ga.sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGal nN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	2010/11/05 21:39
VIII.15	\$ 150 150 150 150 150 150 150 150 150 150	(active or single quantum well or SQW)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	S	2010/11/05 21:38

,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	,	<i></i>		,	,	
L14	107	\ '	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ		2010/11/05 21:36
L13	107	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d} or "80""%") or (5{d} or "80""%") and (InGaN or "In.sub.x Ga.sub.1-x N" or "In.sub.x Ga.sub.1-x N" or "In.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGaInN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	8 8	2010/11/05 21:34
L12	103	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d} or "80")"%" or (5{d} or "8")) and (InGaN or "In.sub.x Ga.sub.1-x N" or "In.subalpha.Ga. sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGaInN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	S	2010/11/05 21:33

L11		(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d} or "80") or (5{d} or ".8")) and (InGaN or "In.sub.x Ga. sub.1-x N" or "In.sub alpha. Ga.sub.1alpha. N") and ("Al.sub.x" "Ga. sub.y" "In.sub.1-x-y" N or AlGaInN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	O	2010/11/05 21:32
L10	73	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) same ((5{d} or "80") or (".5"{d1:2})) and (InGaN or "In.sub.x Ga. sub.1-x N" or "In.sub alpha.Ga.sub.1alpha. N") and ("Al.sub.x" "Ga. sub.y" "In.sub.1-x-y" N or AlGaInN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	O	2010/11/05 21:20
L9	402	(active or single quantum well or SQW) same(grad\$3 or vary\$3 or var\$3)same ((Indium or In) near2 (high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content) and (InGaN or "In.sub. x Ga.sub.1-x N" or "In. subalpha.Ga.sub.1 alpha.N") and ("Al.sub. x" "Ga.sub.y" "In.sub.1-x-y" N or AlGal nN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	O	2010/11/05 20:57

L6	257	(active or single quantum well or SQW) same grad\$3 and ((Indium or In) near2 (high or rich) or (indium or In)) same (composition\$2 or mol or mole or content) and (InGaN or "In.sub. x Ga.sub.1-x N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGaInN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 20:14
L5	255	(active or single quantum well or SQW) same grad\$3 and ((Indium or In) near2 (high or rich) or (indium or In)) same (composition or mol or mole or content) and (InGaN or "In.sub.x Ga. sub.1-x N") and ("Al. sub.x" "Ga.sub.y" "In. sub.1-x-y" N or AlGaInN or GaN or AlGaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 20:06
L4	40	(active or single quantum well or SQW) same grad\$3 and ((Indium or In) near2 (high or rich) or (indium or In)) same (composition or mol or mole or content) and (InGaN or "In.sub.x Ga. sub.1-x N") and ("Al. sub.x" "Ga.sub.y" "In. sub.1-x-y" N or AlGaInN) and GaN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 20:04
L3	40	(active or single quantum well or SQW) same grad\$3 and ((Indium or In) near2 (high or rich) or (indium or In)) same (composition or mol or mole or content) and (InGaN or "In.sub.x Ga. sub.1-x N") and ("Al. sub.x" "Ga.sub.y" "In. sub.1-x-y" N or AlGaInN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 20:03

<u> </u>	110	(active or single quantum well or SQW) same grad\$3 and (Indium or In) near2 (high or rich) and (InGaN or "In.sub.x Ga. sub.1-x N") and ("Al. sub.x" "Ga.sub.y" "In. sub.1-x-y" N or AlGalnN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 19:59
L1	1	(active or single quantum well or SQW) same (Indium or In) near2(high or rich) same grad\$3 and (InGaN or "In.sub.x Ga. sub.1-x N") and ("Al. sub.x" "Ga.sub.y" "In. sub.1-x-y" N or AlGalnN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 19:56
S190	1041	257/e33.008.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 16:56
S189	212	graded same (single quantum well or SQW or active) same indium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 16:37
S188	8	graded same single quantum well same indium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 15:20
S187	20	growth near interruption same indium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 15:10
S186	31	257/e33.03.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 12:20
S185	8	257/e33.031.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 12:19
S184	28	257/e33.026.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 12:15

S183	228	257/e33.025.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 12:11
S182	280	257/e33.023.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:56
S181	20	257/e33.016.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:55
S180	400	257/85.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:44
S179	520	257/9.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:38
S178	140	257/28.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:34
S177	535	257/e29.298.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 11:25
S176	95	single quantum well same graded same (indium or (In))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/05 10:56
S175	94	single quantum well same graded same (indium or (In))	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/11/05 10:55
S174	114	("5247533" "5278435" "5290393" "5306662" "5334277" "5433169" "5468678" "5583879" "5604763" "5625202").PN. OR ("5834331").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/05 10:10

S173	17	(ultra\$violet or UV) near light near emitt\$3 and (high or rich)near (indium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 10:00
S172	217	(ultra\$violet or UV) near light near emitt\$3 and (high or rich)near (indium or In)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 10:00
S171	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.64"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:59
S170	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.63"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S169	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.62"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S168	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.65"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S167	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.9"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S166	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.8"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S165	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.7"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S164	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.58"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S163	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.52"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58

S162	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.51"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S161	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.55"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:58
S160	12	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.5"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:56
S159	0	(ultra\$violet or UV) near light near emitt\$3 and "In.sub.0.6"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:56
S158	10250	(ultra\$violet or UV) near light near emitt\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:56
S157	172	257/e29.033.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:53
S156	106	257/e29.072.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:46
S155	215	257/e29.07.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:46
S154	99	257/e29.069.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 09:40
S153	36	grading with (indium) same (quantum near well or active or QW)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 00:02
S152	1	grading with (indium) and ultraviolet and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 00:01

S151	70	grading with (indium or In)and ultraviolet and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 00:01
S150	4	grading near (indium or In)and ultraviolet and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/05 00:00
S149	300	grading near (indium or In)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/04 23:59
S148	8	"596126".ap.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/11/04 23:06
S147	43	("5617446" "5670798").PN. OR ("5889295").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/04 22:34
S146	147	InGaN and (ultraviolet or UV or ultra-violet) and (indium)same (quantum near well or active) and 257/11-15. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 21:59
S145	333	InGaN and (ultraviolet or UV or ultra-violet) and (indium or In) same (quantum near well or active) and 257/11-15.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 21:50
S144	126	InGaN and (ultraviolet or UV or ultra-violet) and (indium or In) same (quantum near well or active) and 257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 21:50
S143	135	InGaN and (ultraviolet or UV or ultra-violet) and 257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:43
S142	110	InGaN and ultraviolet and 257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:43

S141	251	InGaN and 257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:42
S140	1308	257/14.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:41
S139	7	emitt\$3 same (ultraviolet or ultra- violet or UV) and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:35
S138	0	In near Ga near N and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:25
S137	11	In-rich and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:25
S136	1	In near GaN and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:24
S135	3	InGaN and seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:24
S134	403	seoul national university industry foundation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 18:24
S133	1	((PILKYUNG) near2 (MOON)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/04 18:23
S132	1	((SOON-YONG) near2 (KWON)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/04 18:21
S131	3	((EUIJOON) near2 (YOON)).INV.	US-PGPUB; USPAT; USOCR	OR	ON	2010/11/04 18:18
S130	1	(ultraviolet or UV)emitt \$3 (indium near rich or In near rich) quantum near well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2010/11/04 18:18

S129	0	(ultraviolet or UV)emitt \$3 (indium near rich or In near reach) quantum near well		SAME	ON	2010/11/04 18:18
S128	11	(ultraviolet or UV)emitt \$3 (InGaN or In near Ga near N)near quantum near well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/11/04 18:03
S127	471	(ultraviolet or UV)emitt \$3 (InGaN or In near Ga near N)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/11/04 18:02

EAST Search History (Interference)

Ref#	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L23	47	((luminous or light near emitt\$3 or active or single quantum well or SQW) and(grad\$3 or vary\$3 or var\$3) same ((Indium or In) near2(high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content)same ((5 {d} "%" or "80""%") or ("0.5" or "0.6" or "0.7" or "0.8"))and (InGaN or "In.sub.x Ga.sub.1-x N" or "In. subalpha.Ga.sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGalnN or GaN or AlGaN))and 257/9-15,E29.069,E29.07,E29.072,E29.033,E33.016,E33.023,E33.025,E33.026,E33.031,E33.03,E33.033,E33.008,94,96,97,103,21.ccls.	US- PGPUB; USPAT; UPAD	ADJ	ON	2010/11/05 21:55
L22	2	((luminous or light near emitt\$3 or active or single quantum well or SQW)and(grad\$3 or vary\$3 or var\$3) and ((Indium or In) near2(high or rich) or (indium or In)) and (concentration or composition\$2 or mol or mole or content)same ((5 {d} "%" or "80""%") or ("0.5" or "0.6" or "0.7" or "0.8"))and (InGaN or "In.sub.x Ga.sub.1-x N" or "In. subalpha.Ga.sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGaInN or GaN or AlGaN)). clm.	US- PGPUB; USPAT; UPAD	ADJ	ON	2010/11/05 21:51

21	0	((luminous or light near emitt\$3 or active or single quantum well or SQW)same(grad\$3 or vary\$3 or var \$3)same ((Indium or In) near2(high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content)same ((5 {d} "%" or "80""%") or ("0.5" or "0.6" or "0.7" or "0.8"))and (InGaN or "In.sub.x Ga.sub.1-x N" or "In. subalpha.Ga.sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGaInN or GaN or AlGaN)). clm.	US- PGPUB; USPAT; UPAD	ADJ	ON	2010/11/05 21:50
L20	45	(luminous or light near emitt\$3 or active or single quantum well or SQW)same(grad\$3 or vary\$3 or var \$3)same ((Indium or In) near2(high or rich) or (indium or In)) same (concentration or composition\$2 or mol or mole or content)same ((5 {d} "%" or "80""%") or ("0.5" or "0.6" or "0.7" or "0.8"))and (InGaN or "In.sub.x Ga.sub.1-x N" or "In. subalpha.Ga.sub.1alpha.N") and ("Al.sub.x" "Ga.sub.y" "In.sub.1-x-y" N or AlGaInN or GaN or AlGaN)	US- PGPUB; USPAT; UPAD	ADJ	ON .	2010/11/05 21:50

11/ 5/ 2010 10:19:05 PM H:\ Workspaces\ 10596126.wsp